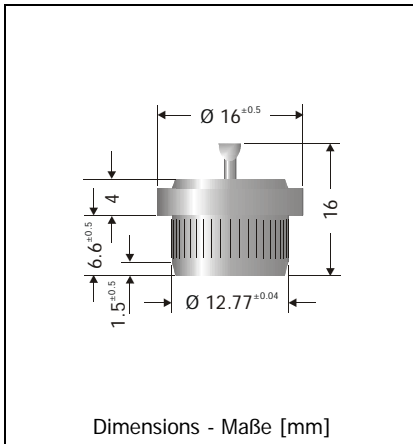


KYZ35A05 ... KYZ35A6, KYZ35K05 ... KYZ35K6

**Silicon-Press-Fit-Diodes – High Temperature Diodes
Silizium-Einpress-Dioden – Hochtemperatur-Dioden**

Version 2006-04-22



Nominal Current 35 A
 Nennstrom
 Repetitive peak reverse voltage 50 ... 600 V
 Periodische Spitzensperrspannung
 Metal press-fit case with glass seal
 Metall-Einpressgehäuse mit Glas-Durchführung
 Weight approx. – Gewicht ca. 10 g
 Compound has classification UL94V-0
 Vergussmasse nach UL94V-0 klassifiziert
 Standard packaging: bulk
 Standard Lieferform: lose im Karton



Maximum ratings

Grenzwerte

| Type / Typ Wire to / Draht an | | Repetive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] | Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V] |
|----------------------------------|----------|--|---|
| Anode | Cathode | | |
| KYZ35A05 | KYZ35K05 | 50 | 60 |
| KYZ35A1 | KYZ35K1 | 100 | 120 |
| KYZ35A2 | KYZ35K2 | 200 | 240 |
| KYZ35A3 | KYZ35K3 | 300 | 360 |
| KYZ35A4 | KYZ35K4 | 400 | 480 |
| KYZ35A6 | KYZ35K6 | 600 | 700 |

| | | | |
|--|---------------------------|----------------|------------------------------|
| Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last | $T_C = 100^\circ\text{C}$ | I_{FAV} | 35 A |
| Repetitive peak forward current Periodischer Spitzenstrom | $f > 15\text{ Hz}$ | I_{FRM} | 130 A ¹⁾ |
| Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwellen | $T_A = 25^\circ\text{C}$ | I_{FSM} | 360/400 A |
| Rating for fusing, $t < 10\text{ ms}$ Grenzlastintegral, $t < 10\text{ ms}$ | $T_A = 25^\circ\text{C}$ | i^2t | 660 A ² s |
| Operating junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur | | T_j T_s | -50...+175°C -50...+175°C |

1 Max. case temperature $T_C = 150^\circ\text{C}$ – Max. Gehäusetemperatur $T_C = 150^\circ\text{C}$

Characteristics

Kennwerte

| | | | |
|--|--|-----------|---------------------|
| Forward Voltage Durchlass-Spannung | $T_j = 25^\circ\text{C}$ $I_F = 35\text{ A}$ | V_F | < 1.1 V |
| Leakage Current Sperrstrom | $T_j = 25^\circ\text{C}$ $V_R = V_{RRM}$ | I_R | < 100 μA |
| Thermal Resistance Junction – Case Wärmewiderstand Sperrschicht – Gehäuse | | R_{thc} | < 0.8 K/W |

